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cont.

A ceramic heater used in an industrial field of semiconductors of the second aspect of the present invention, comprises a disk-shaped ceramic substrate; and a heat-generation pattern disposed within said disk-shaped ceramic substrate, wherein the disk-shaped ceramic substrate has a thickness of 18 mm or less and the ceramic substrate is made of at least one selected from the group essentially consisting of ceramic nitride and ceramic carbide; and the heat-generation pattern has a bending portion which describes an arc having a curvature radius within a range of 0.1 to 20 mm.

In these cases, the heat-generation pattern may preferably have a width within a range of 0.1 to 20 mm and may preferably be a combination of a spiral pattern and a bending pattern. Alternatively, the heat-generation pattern may preferably be a combination of a spiral pattern and a bending pattern; and the bending pattern may preferably be arranged along the outer regions of the disk-shaped ceramic substrate.

IN THE CLAIMS:

Please replace claims 1-4 as follows:

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(Amended) A ceramic heater used in an industrial field of semiconductors, comprising:

a disk-shaped ceramic substrate; and

a heat-generation pattern disposed on a surface of said disk-shaped ceramic substrate,

wherein said disk-shaped ceramic substrate has a thickness of 18 mm or less and said ceramic substrate is made of at least one selected from a group essentially consisting of ceramic nitride and ceramic carbide; and

said heat-generation pattern has a bending portion which describes an arc having a curvature radius within a range of 0.1 mm to 20 mm.

2. (Amended) A ceramic heater used in an industrial field of semiconductors, comprising:
a disk-shaped ceramic substrate; and
a heat-generation pattern disposed within said disk-shaped ceramic substrate, wherein said disk-shaped ceramic substrate has a thickness of 18 mm or less and said ceramic substrate is made of at least one selected from a group essentially consisting of ceramic nitride and ceramic carbide; and
said heat-generation pattern has a bending portion which describes an arc having a curvature radius within a range of 0.1 to 20 mm.

3. (Amended) The ceramic heater used in an industrial field of semiconductors, according to claim 1, wherein said heat-generation pattern has a width within a range of 0.1 to 20 mm.

4. (Amended) The ceramic heater used in an industrial field of semiconductors, according to claim 1, wherein said heat-generation pattern is a combination of a spiral pattern and a bending pattern.

Please add new claims 5-8 as follows:

--5. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 1, wherein said heat-generation pattern is a combination of a spiral pattern and a bending pattern, and said bending pattern is arranged along outer regions of said disk-shaped ceramic substrate.--

--6. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 2, wherein said heat-generation pattern has a width within a range of 5 to 20 μm --

--7. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 2, wherein said heat-generation pattern is a combination of a spiral pattern and a bending pattern.--